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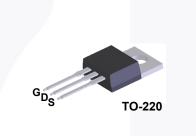
FQP44N10 N-Channel QFET[®] MOSFET 100 V, 43.5 A, 39 mΩ

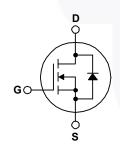
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- + 43.5 A, 100 V, $R_{DS(on)}$ = 39 m Ω (Max.) @V_{GS} = 10 V, I_{D} = 21.75 A
- Low Gate Charge (Typ. 48 nC)
- Low Crss (Typ. 85 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

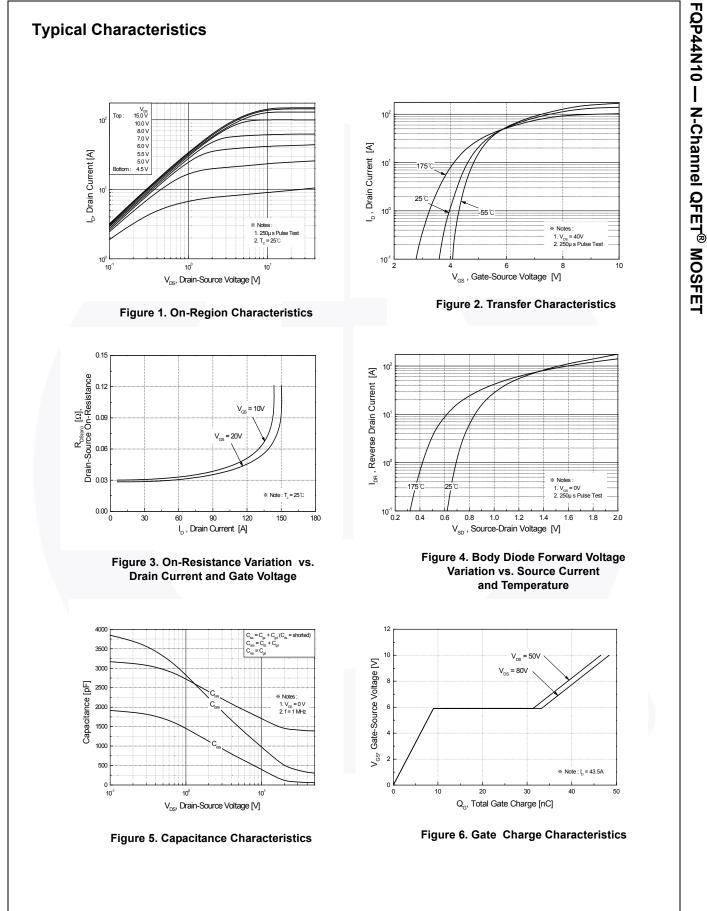
Symbol	Parameter		FQP44N10	Unit
V _{DSS}	Drain-Source Voltage		100	V
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		43.5	A
	- Continuous (T _C = 100°C)		30.8	A
I _{DM}	Drain Current - Pulsed	(Note 1)	174	A
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	530	mJ
I _{AR}	Avalanche Current	(Note 1)	43.5	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	14.6	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	6.0	V/ns
P _D	Power Dissipation (T _C = 25°C)		146	W
	- Derate above 25°C		0.97	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
т	Maximum Lead Temperature for Soldering,		300	°C
ΤL	1/8" from Case for 5 seconds		300	C

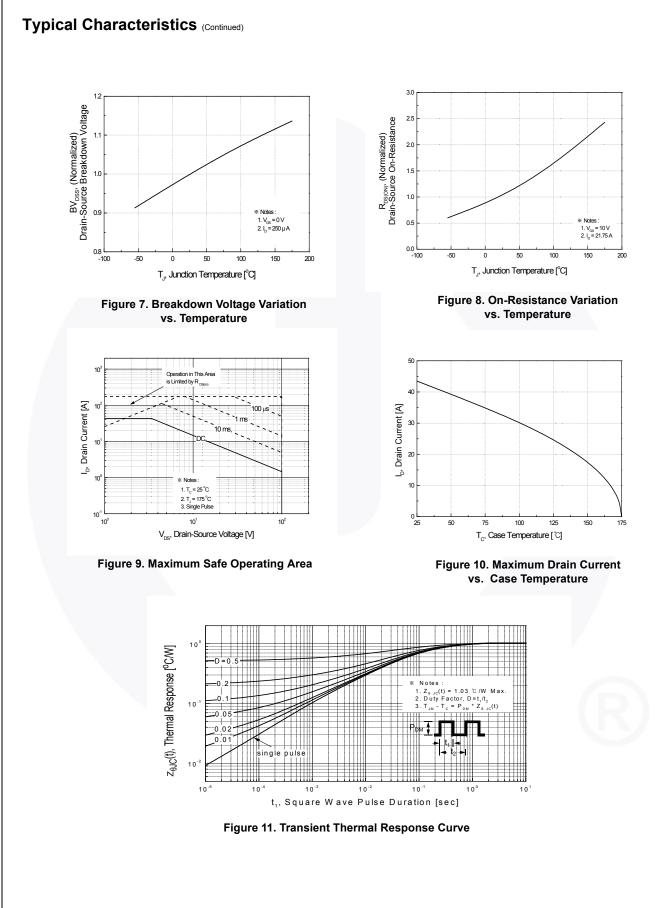
Thermal Characteristics

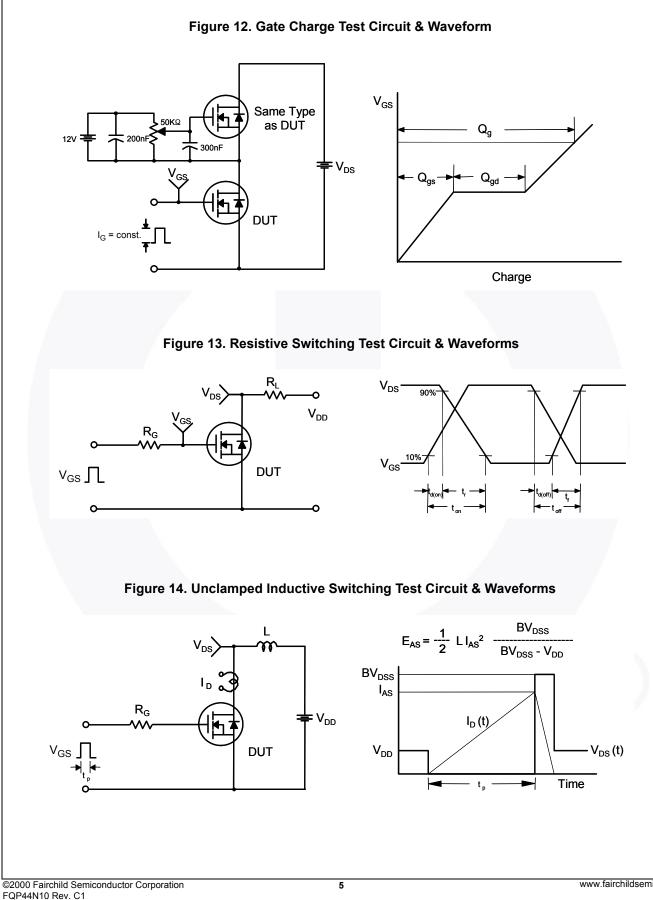
Symbol	Parameter	FQP44N10	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.03	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

November 2013

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otes:	t _{rr}	Reverse R	ecovery Time		V _G	_S = 0 V, I _S = 43.5 A,			98		ns
otes:	Q _{rr}	Reverse R	ecovery Charge		dl _F	/ dt = 100 A/µs			360		nC
Repetitive Rating : Pulse width limited by maximum junction temperature. L = 0.42 mH, $I_{AS} = 43.5 \text{ A}$, $V_{DD} = 25 \text{ V}$, $R_G = 25 \Omega$, starting $T_J = 25^{\circ}\text{C}$. $I_{SD} \le 43.5 \text{ A}$, di/dt $\le 300 \text{ A/}\mu\text{s}$, $V_{DD} \le BV_{DSS}$, starting $T_J = 25^{\circ}\text{C}$. Essentially independent of operating temperature.	Repetitive R L = 0.42 mH $I_{SD} \le 43.5$	I, I_{AS} = 43.5 A, V A, di/dt \leq 300 A/	$_{DD}$ = 25 V, R _G = 25 Ω , starting μ s, V _{DD} \leq BV _{DSS} , starting T _J =	「」= 25°C.							







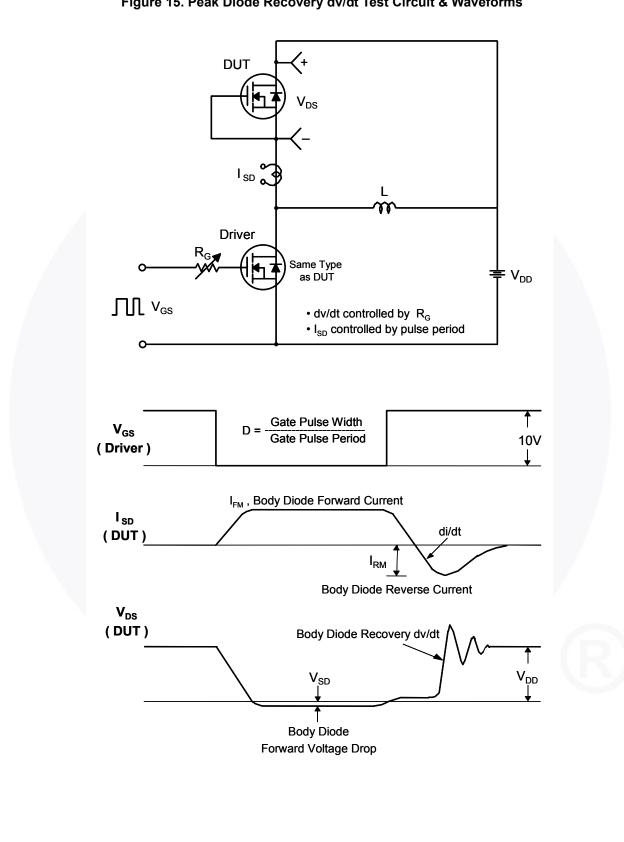
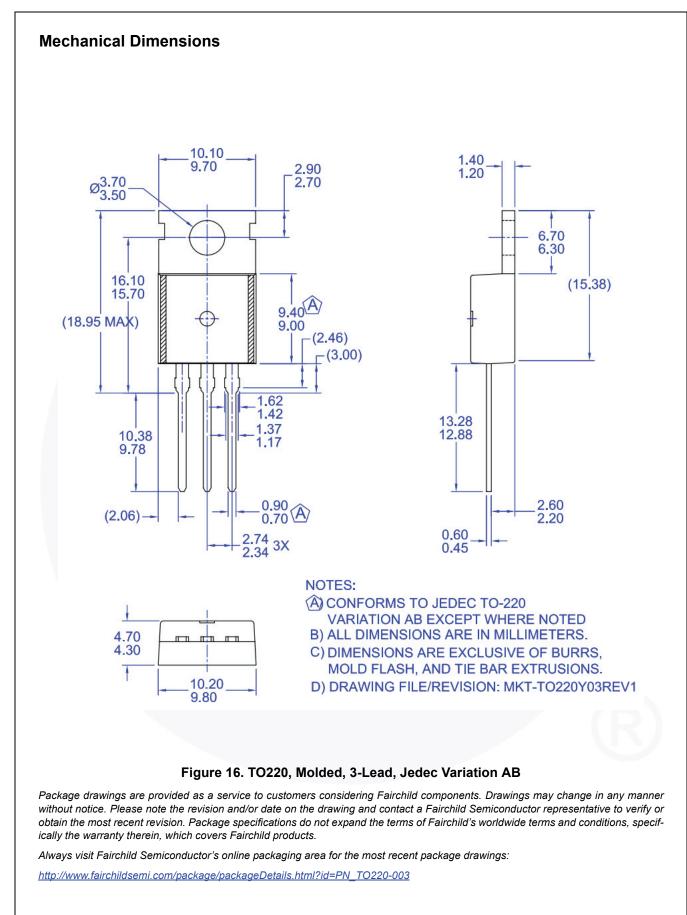


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





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